

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	5025	382/149,145,224,159,100,141,155,181.CQLS.	USPAT	OR	ON	2009/06/29 11:58
L2	4478	715/774,835,837,764,841,210,839,762,809,804,973,250,866,708.CQLS.	USPAT	OR	ON	2009/06/29 12:01
L3	1453	719/310,315.CQLS.	USPAT	OR	ON	2009/06/29 12:01
L4	355	714/E11.21.CQLS.	USPAT	OR	ON	2009/06/29 12:02
L5	1846	356/237.1,237.2.CQLS.	USPAT	OR	ON	2009/06/29 12:03
L6	834	702/35,1,33.CQLS.	USPAT	OR	ON	2009/06/29 12:04
L7	599018	(wafer\$1 or semiconductor\$1 or chip\$1 or substrat\$1)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 12:29
L8	125	L7 and user adj select\$3 and review and data adj file	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 12:32
L9	3	L8 and input adj user and page and learning adj mode and parameters	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 12:34
L10	4	L8 and input and user and page and learning adj mode and parameters	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 12:37
L11	4	L8 and learning adj mode and parameters	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 12:55

L12	1	L8 and automatic adj defect and recognition and(detect\$3 or determining)/and(defect or flaw or fault)/and(assign\$3 or test\$3 or evaluat\$3)and descriptor	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 12:58
L13	11	automatic adj defect and recognition and(detect\$3 or determining)/and(defect or flaw or fault)/and(assign\$3 or test\$3 or evaluat\$3)and descriptor	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 12:59
L14	10	L13 and(wafer\$1 or semiconductor\$1 or chip\$1 or substrat\$1)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 12:59
L15	1	L14 and user adj select\$3 and review and data adj file	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 13:00
L16	1	L14 and user adj select\$3 and review adj data	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 13:00
L17	3	automatic adj defect and recognition and(detect\$3 or determining)/and(defect or flaw or fault)/and(assign\$3 or test\$3 or evaluat\$3 or accept\$3)and select\$3 adj(wafer\$1 or semiconductor\$1 or chip\$1 or substrat\$1)and(capturing or pictures or cod or camera)and (illumination or source or light or optimal adj intensity or light adj intensity)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 13:12
L18	3	automatic adj defect and recognition and(detect\$3 or determining)/and(defect or flaw or fault)/and(assign\$3 or test\$3 or evaluat\$3 or accept\$3)and select\$3 adj(wafer\$1 or semiconductor\$1 or chip\$1 or substrat\$1)and(capturing or pictures or cod or camera)and align\$4 and(illumination or source or light or optimal adj intensity or light adj intensity or brightness or contrast)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 13:16
L19	0	L18 and(@ad<"20030712" or @rlad<"20030712" or @prad<"20030712" or @ptad<"20030712")	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 13:17
S1	571947	(wafer\$1 or semiconductor\$1 or chip\$1 or substrat\$1)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:27

S2	1	S1 and automatic and defect adj classification and teaching and knowledge adj based adj database	US-PGPRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:29
S3	1	automatic and defect adj classification and teaching and knowledge adj based adj database	US-PGPRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:30
S4	1	S1 and defect adj classification and teaching and knowledge adj based adj database	US-PGPRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:30
S5	1	defect adj classification and teaching and knowledge adj based adj database	US-PGPRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:30
S6	2	defect adj classification and knowledge adj based adj database	US-PGPRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:31
S7	82	defect and classification and knowledge adj database	US-PGPRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:31
S8	19	S7 and (water\$1 or semiconductor\$1 or chip\$1 or substrat\$1)	US-PGPRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:31
S9	17	S8 and(@ad<"20030712" or @rlad<"20030712" or @prad<"20030712" or @ptad<"20030712")	US-PGPRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:36
S10	12	S8 and @ad<"20030712"	US-PGPRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:36

S11	24	((DIRK) near2 (SOENKSEN)).INV.	US-PGPUB; USPAT	OR	ON	2008/12/05 11:36
S12	11	((RALF) near2 (FRIEDRICH)).INV.	US-PGPUB; USPAT	OR	ON	2008/12/05 11:37
S13	1	((ANDREAS) near2 (DRAEGER)).INV.	US-PGPUB; USPAT	OR	ON	2008/12/05 11:37
S14	2	((DETLEF) near2 (SCHUPP)).INV.	US-PGPUB; USPAT	OR	ON	2008/12/05 11:37
S16	2	((THIN) near2 ("VAN LUU")).INV.	US-PGPUB; USPAT	OR	ON	2008/12/05 11:39
S17	3	((WOLFGANG) near2 (LANGER)).INV.	US-PGPUB; USPAT	OR	ON	2008/12/05 11:39
S18	0	S11 and defect and classification and knowledge adj database	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:40
S19	0	S11 and defect and classification and knowledge adj database	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:40
S20	0	S11 and defect and classification and knowledge adj database	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:41
S21	0	S12 and defect and classification and knowledge adj database	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:41
S22	0	S13 and defect and classification and knowledge adj database	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:43
S23	3	S10 and descriptor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:46

S24	638382	S23 and select\$3 and review and data file	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/05 11:47
S25	0	S23 and select\$3 and review and data adj file	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/05 11:47
S26	18	S7 and select\$3 and review and data adj file	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/05 11:48
S27	0	S26 and parameters and learning adj node	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/05 11:49
S28	0	S26 and parameters and learning adj mode	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/05 11:49
S29	17	S26 and parameters	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/05 11:49
S30	2	S1 and S7 and S24 and S29	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/05 11:56
S31	2	S30 and @ad<"20030712"	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/05 11:56
S32	18	S7 and S26	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/05 11:57

S33	16	S32 and @ad<"20030712"	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/05 11:58
S34	20	S1 and automatic and defect adj recognition	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/05 12:00
S35	638382	S34 and select\$3 and review and data file	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/05 12:01
S36	4	S34 and descriptor	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/05 12:33
S37	1	S34 and learning adj mode	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/05 12:34
S38	0	S37 and @ad<"20030712"	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/05 12:34
S39	16	S34 and @ad<"20030712"	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/05 12:35
S40	0	S39 and learning adj mode	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/05 12:35
S41	2	S39 and learning	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/05 12:35

S42	16	S26 and @ad<"20030712"	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 12:39
S43	0	S42 and learning adj mode	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 12:40
S44	0	S42 and learning near mode	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 12:40
S45	0	S42 and learning near3 mode	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 12:40
S46	11	S42 and descriptor	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 12:40
S47	598	S1 and select\$3 and review and data adj file	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 12:44
S48	340	S47 and @ad<"20030712"	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 12:44
S49	1	S48 and input and user and learning adj mode	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 12:45
S50	1	S48 and learning adj mode	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 12:46

S51	4	S48 and alignment adj procedure	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 12:46
S52	0	S8 and automatic adj defect and recognition and(detect\$3 or determining)same (defect or flaw or fault)same(assign\$3 or test\$3 or evaluat\$3)same descriptor	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 13:02
S53	0	S48 and automatic adj defect and recognition and(detect\$3 or determining)same (defect or flaw or fault)same(assign\$3 or test\$3 or evaluat\$3)same descriptor	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 13:02
S54	1	automatic adj defect and recognition and(detect\$3 or determining)same (defect or flaw or fault)same(assign\$3 or test\$3 or evaluat\$3)same descriptor	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 13:02
S55	11	automatic adj defect and recognition and(detect\$3 or determining)and(defect or flaw or fault)and(assign\$3 or test\$3 or evaluat\$3)and descriptor	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 13:03
S56	5	S55 and @ad<"20030712"	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 13:03
S57	1	S56 and learning adj mode	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 13:03
S58	0	S57 and edit adj recipe	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 13:05
S59	0	S57 and edit	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 13:05



S60	0	S67 and memory adj circuits	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 13:07
S61	1	S67 and circuits	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 13:07
S62	0	S61 and logic adj circuits	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 13:08
S63	0	S61 and blank adj wafer\$1	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 13:08
S64	1	S66 and learning adj mode	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 14:02
S65	571947	(wafer\$1 or semiconductor\$1 or chip\$1 or substrat\$1)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:12
S66	2	S65 and select\$3 and review adj data adj file	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:13
S67	2	S65 and review adj data adj file	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:13
S68	638	S65 and review and data adj file	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:14

S69	134	S65 and review same data adj file	US-PG&UB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:14
S70	0	S69 and defect and classification and knowledge adj database	US-PG&UB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:15
S71	0	S69 and classification and knowledge adj database	US-PG&UB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:15
S72	1	S69 and classification and knowledge near3 database	US-PG&UB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:15
S73	11	S68 and classification and knowledge near3 database	US-PG&UB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:15
S74	5	S73 and @ad<"20030712"	US-PG&UB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:16
S75	5	S74 and review and data adj file	US-PG&UB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:16
S76	1	S75 and (user or operator or human)and page and learning adj mode	US-PG&UB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:17
S77	1	S75 and (user or operator or human)and learning adj mode	US-PG&UB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:17

S78	9	S68 and (detect\$3 or determining) and (defect or fault or flaw) and classification and knowledge near3 database	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:19
S79	13	learning and (knowledge-based or knowledge adj based) and database and automatic and defect adj classification	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:21
S80	10	S79 and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:21
S81	0	S80 and review and data adj file	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:21
S82	1	S80 and data adj file	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:22
S83	8	S80 and (wafer\$1 or semiconductor\$1 or chip\$1 or substrat\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:24
S84	8	S83 and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:24
S85	6	S84 and descriptor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:43
S86	5	S84 and descriptor adj (defect or fault or flaw)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:46

S87	573639	(wafer\$1 or semiconductor\$1 or chip\$1 or substrat\$1)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:04
S88	19	S87 and defect and classification and knowledge adj database	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:05
S89	640949	S88 and select\$3 and review and data file	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:05
S90	2	S88 and select\$3 and review and data adj file	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:05
S91	8	S87 and display adj thumbnails	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:07
S92	2	S91 and @ad<"20030712"	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:07
S93	0	S92 and descriptor	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:15
S94	8	S91 and parameters	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:27
S95	1	S94 and automatic adj defect and recognition and(detect\$3 or determining)and(defect or flaw or fault)and(assign\$3 or test\$3 or evaluat\$3)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:29

S96	2	S92 and display adj thumbnails	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/17 19:30
S97	2	S96 and parameters	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/17 19:30
S98	0	S97 and circuits	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/17 19:31
S99	0	S97 and defect and (classification or classifier or classify)	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/17 19:32
S100	0	S97 and(classification or classifier or classify or grouping)	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/17 19:33
S101	0	S97 and intensity	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/17 19:33
S102	2	S97 and (intensity or contrast or brightness)	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/17 19:34
S103	2	S102 and(illumination or source or light)	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/17 19:34
S104	2	S103 and(blank adj wafer\$1 or wafer\$1)	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/17 19:36

S105	2	S104 and (polymer or layer or oxide adj layer or contact or metal)	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/17 19:38
S106	0	S105 and lens	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/17 19:39
S107	0	S105 and focus	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/17 19:39
S108	0	S105 and magnificat\$3	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/17 19:40
S109	2	S105 and @ad< "20030712"	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/17 19:40
S110	2	S109 and select\$3 adj recipe	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/17 19:41
S111	2	"6973209".pn.	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/19 15:40
S112	0	S111 and alignment	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/19 15:40
S113	1	S111 and align\$3	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/19 15:40

S114	0	S111 and align\$3 same light	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 15:41
S115	1	S111 and align\$3 and(light or source or illuminat\$3)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 15:41
S116	1	S115 and adjusting	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 15:42
S117	0	S116 and optimal adj intensity	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 15:42
S118	1	S116 and optimal	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 15:42
S119	0	S118 and intensity	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 15:42
S120	1	S118 and parameters	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 15:43
S121	1	S120 and algorithm	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 15:46
S122	1	S121 and automatic	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 15:47

S123	0	S122 and intensity	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/19 15:47
S124	1	S122 and (intensity or contrast or brightness)	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/19 15:47
S125	0	S124 and text adj image\$1	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/19 15:48
S126	0	S124 and text	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/19 15:48
S127	1	S124 and recipe	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/19 15:49
S128	0	S127 and review	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/19 15:49
S129	1	S127 and dictionary	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/19 15:49
S130	1	S129 and registered	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/19 15:50
S131	1	S130 and drag	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/19 15:51



S132	82	defect and classification and knowledge adj database	US-PG&UB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 16:09
S133	18	S132 and select\$3 and review and data adj file	US-PG&UB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 16:09
S134	16	S133 and @ad< "20030712"	US-PG&UB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 16:09
S135	0	S132 and select\$3 same review adj data	US-PG&UB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 16:13
S136	5	S132 and review adj data	US-PG&UB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 16:13
S137	3	S136 and @ad< "20030712"	US-PG&UB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 16:14
S138	1	S137 and descriptors	US-PG&UB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 16:19
S139	0	S137 and defect adj descriptors	US-PG&UB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 16:20
S140	82	defect and classification and knowledge adj database	US-PG&UB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 11:44

SI41	5	SI40 and review adj data	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/30 11:44
SI42	3	SI41 and @ad< "20030712"	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/30 11:44
SI43	2	SI42 and(wafer\$1 or semiconductor\$1 or chip\$1 or substrat\$1)	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/30 11:45
SI44	3	"6408219".pn.	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/30 11:46
SI45	1	SI44 and review adj data	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/30 11:47
SI46	1	SI44 and select\$3	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/30 11:48
SI47	732	select\$3 same review adj data	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/30 11:50
SI48	62	SI47 and(wafer\$1 or semiconductor\$1 or chip\$1 or substrat\$1)	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/30 11:50
SI49	0	SI48 and defect and classification and knowledge adj database	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/30 11:50

SI50	0	SI48 and classification and knowledge adj database	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 11:50
SI51	14	SI48 and @ad< "20030712"	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 11:51
SI52	0	SI51 and display adj thumbnails	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 11:51
SI53	0	SI51 and display and thumbnails	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 11:52
SI54	0	SI51 and thumbnails	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 11:52
SI55	0	SI51 and automatic and defect adj recognition	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:12
SI56	0	SI51 and select\$3 adj recipe	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:13
SI57	1	SI51 and align\$3 and (light or source or illuminat\$3)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:13
SI58	0	SI57 and (user or operator or human) and page and learning adj mode	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:16

SI59	0	SI57 and descriptors	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:16
SI60	0	SI57 and parameters	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:36
SI61	11	automatic adj defect and recognition and(detect\$3 or determining)and(defect or flaw or fault)and(assign\$3 or test\$3 or evaluat\$3)and descriptor	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 15:58
SI62	5	SI61 and @ad< "20030712"	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 15:58
SI63	1	SI62 and learning adj mode	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 15:58
SI64	0	SI63 and memory adj circuits	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 15:58
SI65	575216	(wafer\$1 or semiconductor\$1 or chip\$1 or substrat\$1)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 15:58
SI66	10	SI65 and automatic adj defect and recognition and(detect\$3 or determining)and(defect or flaw or fault)and(assign\$3 or test\$3 or evaluat\$3)and descriptor	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 15:59
SI67	643423	SI66 and select\$3 and review and data file	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 15:59

SI68	1	SI66 and select\$3 and review and data adj file	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/31 16:00
SI69	0	SI68 and @ad<"20030712"	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/31 16:00
SI70	1	SI66 and memory adj circuits	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/31 16:00
SI71	0	SI70 and @ad<"20030712"	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/31 16:01
SI72	4	SI66 and @ad<"20030712"	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/31 16:01
SI73	0	SI72 and memory adj circuits	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/31 16:01
SI74	7745	SI65 and memory adj circuits	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/31 16:01
SI75	2341	SI74 and parameters	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/31 16:01
SI76	775	SI75 and logic adj circuits	US-PGRUB; USPAT; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2008/12/31 16:02

S177	9	S176 and blank adj wafer	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:02
S178	8	S177 and @ad< "20030712"	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:03
S179	0	S178 and resist	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:03
S180	0	S178 and photo adj resist	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:03
S181	0	S178 and polymer adj layer	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:04
S182	51765	polymer adj layer	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:04
S183	33269	S182 and @ad< "20030712"	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:04
S184	2388	S183 and oxide adj layer	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:05
S185	1703	S184 and contact	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:05

S186	16332	S183 and contact	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:05
S187	10	S186 and metal adj later	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:06
S188	1	S187 and parameters	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:06
S189	1	S188 and @ad<"20030712"	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:06
S190	1	S189 and(intensity or contrast or brightness)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:07
S191	0	S190 and align\$3 and(light or source or illuminat\$3)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:07
S192	1	S190 and(light or source or illuminat\$3)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:07
S193	0	S192 and magnificat\$3	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:08
S194	0	S192 and lens	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:08

S195	0	S192 and histogram	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:08
S196	0	S195 and focus\$3	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:12
S197	51832	polymer adj layer	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:04
S198	33269	S197 and @ad< "20030712"	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:04
S199	16332	S198 and contact	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:04
S200	10	S199 and metal adj later	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:04
S201	1	S200 and parameters	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:04
S202	1	S201 and @ad< "20030712"	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:04
S203	1	S202 and(intensity or contrast or brightness)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:04



S204	1	S203 and(light or source or illuminat\$3)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:04
S205	0	S204 and metal adj layer	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:05
S206	1	S204 and metal	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:06
S207	0	S206 and bright adj field	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:07
S208	0	S206 and bright	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:07
S209	1	S206 and (UV or DUV)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:08
S210	0	S209 and lens	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:08
S211	0	S209 and intensity	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:09
S212	1	S209 and contrast	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:10

S213	0	S212 and histogram	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:10
S214	795256	select\$3 and review and data file	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:12
S215	2665	S214 and polymer adj layer	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:13
S216	12	S215 and bright adj field	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:13
S217	9	S216 and (UV or DUV)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:13
S218	3	S217 and @ad<"20030712"	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:13
S219	3	S218 and intensity	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:13
S220	0	S219 and histogram	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:14
S221	0	S219 and metal adj layer	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:14

S222	0	S219 and lens	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:14
S223	4	S216 and lens	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:15
S224	0	S223 and @ad< "20030712"	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:15
S225	0	S223 and @ad< "20030712"	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:15

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